

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

Product profile 1.

1.1 General description

Enhanced ultrafast power diode in a TO252 (DPAK) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on-state losses
- Low thermal resistance

- Soft recovery characteristic
- Surface-mountable package

1.3 Applications

Dual Mode (DCM and CCM) PFC

■ Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_{mb} \le 121$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	5	Α
Static char	acteristics					
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C};$ see Figure 5	-	1.3	1.9	V
		$I_F = 5 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 5	-	1.1	1.7	V
Dynamic c	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	17.5	35	ns



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		
2	K	cathode[1]	mb	K — A 001aaa020
3	Α	anode		
mb	К	mounting base; cathode	1 3	
			TO252 (DPAK)	

[1]It is not possible to connect to pin 2 of the TO252 package.

3. Ordering information

Table 3. Ordering information

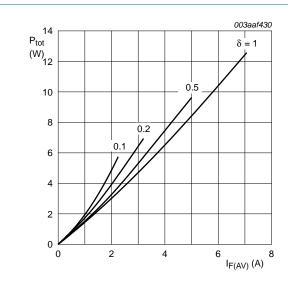
Type number	Package		
	Name	Description	Version
BYV25FD-600	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

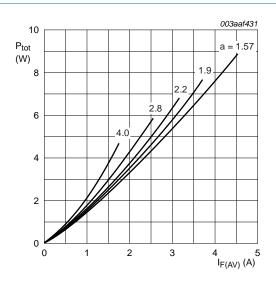
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; $T_{mb} \le 121$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	5	A
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 121 °C	-	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; see <u>Figure 3</u>	-	60	Α
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; see <u>Figure 3</u>	-	66	Α
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	150	°C



$$I_{F(\!AV)} = I_{F(\!R\!MS)} imes \sqrt{oldsymbol{\delta}}$$

 $V_0 = 1.499 \text{ V}; R_s = 0.041 \Omega$

Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a =form factor $= I_{F(RMS)} / I_{F(AV)}$

 $V_o = 1.499 \text{ V}; R_s = 0.041 \Omega$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

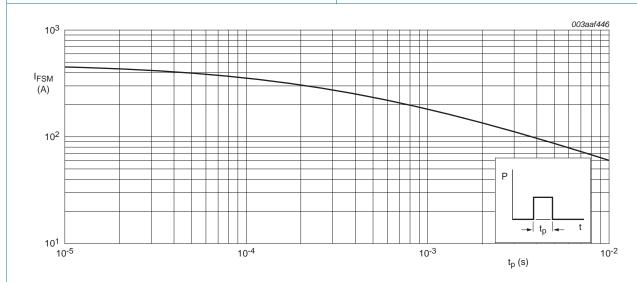


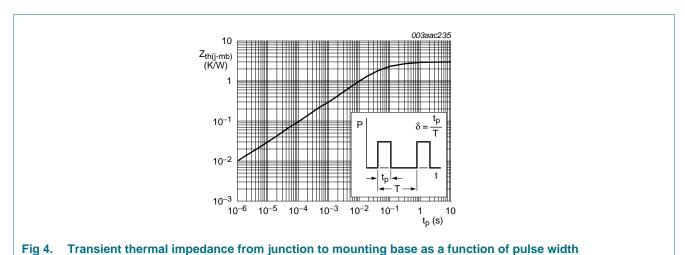
Fig 3. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	see Figure 4	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	50	-	K/W

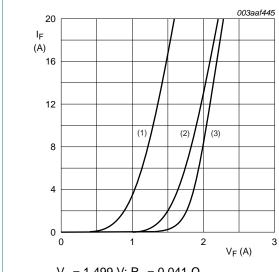
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	Static characteristics						
V_{F}	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.3	1.9	V	
		$I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.1	1.7	V	
I _R	reverse current	V _R = 600 V; T _j = 100 °C	-	-	1.5	mA	
		V _R = 600 V; T _j = 25 °C	-	-	50	μΑ	
Dynamic ch	naracteristics						
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{}$	-	13	-	nC	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_j = 25 \text{ °C}$; see Figure 6	-	17.5	35	ns	
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 ^{\circ}\text{C}$; see Figure 6	-	1.5	-	Α	
V_{FRM}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 7	-	3.2	-	V	



 V_o = 1.499 V; R_s = 0.041 Ω

(1) T_i = 150 °C; typical values;

(2) T_i = 150 °C; maximum values;

(3) T_i = 25 °C; maximum values;

Fig 5. Forward current as a function of forward voltage

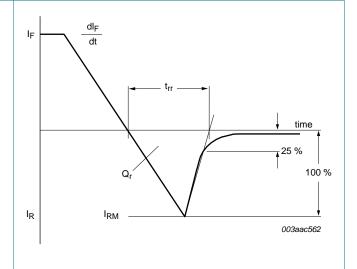
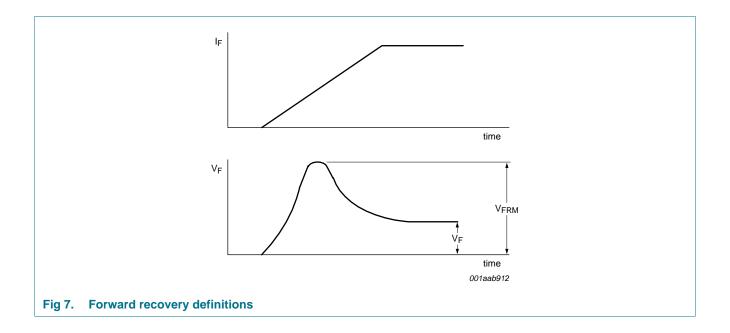
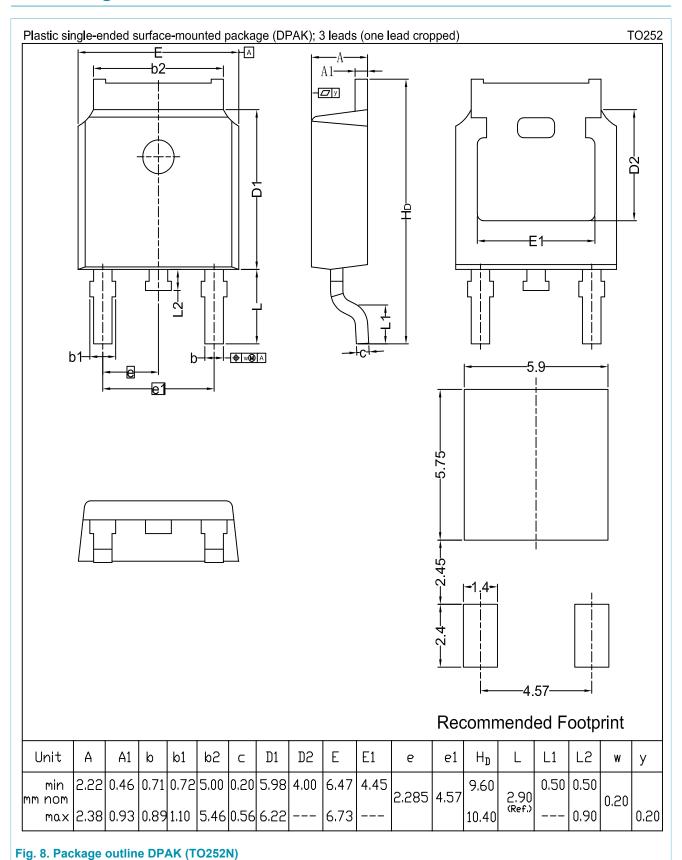


Fig 6. Reverse recovery definitions; ramp recovery



7. Package outline





8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25FD-600 v.2	20110307	Product data sheet	-	BYV25FD-600 v.1
Modifications:	 Various chang 	es to content.		
BYV25FD-600 v.1	20101001	Product data sheet	-	-

9. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Enhanced ultrafast power diode

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